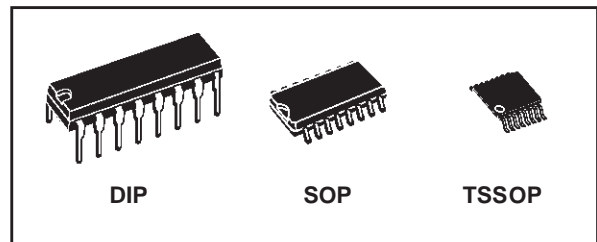




# M74HC75

## 4 BIT D TYPE LATCH

- HIGH SPEED :  
 $t_{PD} = 11\text{ns}$  (TYP.) at  $V_{CC} = 6\text{V}$
- LOW POWER DISSIPATION:  
 $I_{CC} = 2\mu\text{A}$  (MAX.) at  $T_A = 25^\circ\text{C}$
- HIGH NOISE IMMUNITY:  
 $V_{NIH} = V_{NIL} = 28\% V_{CC}$  (MIN.)
- SYMMETRICAL OUTPUT IMPEDANCE:  
 $|I_{OH}| = I_{OL} = 4\text{mA}$  (MIN)
- BALANCED PROPAGATION DELAYS:  
 $t_{PLH} \approx t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE:  
 $V_{CC}$  (OPR) = 2V to 6V
- PIN AND FUNCTION COMPATIBLE WITH  
 74 SERIES 75



### ORDER CODES

PACKAGE	TUBE	T & R
DIP	M74HC75B1R	
SOP	M74HC75M1R	M74HC75RM13TR
TSSOP		M74HC75TTR

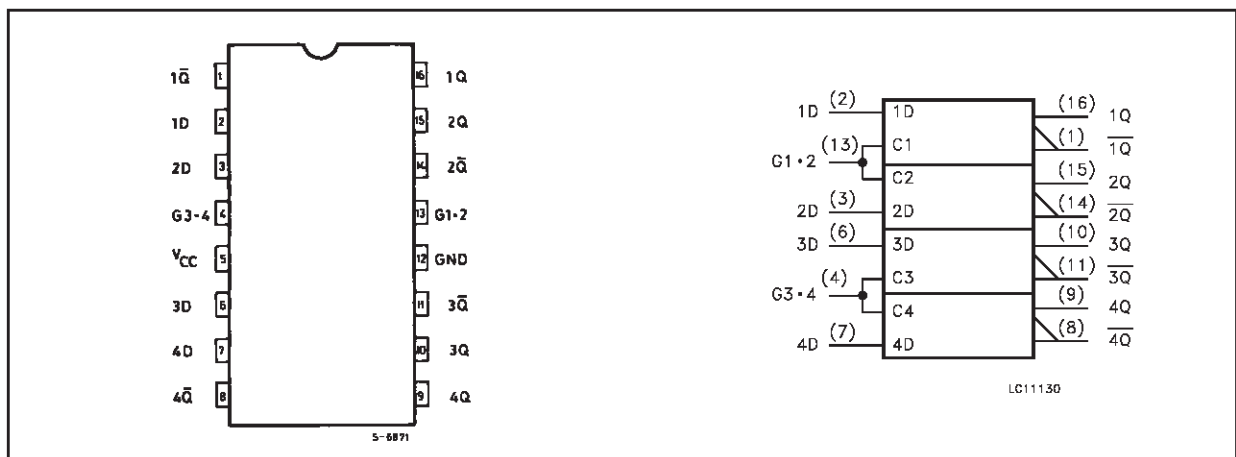
### DESCRIPTION

The M74HC75 is an high speed CMOS 4 BIT D TYPE LATCH fabricated with silicon gate C<sup>2</sup>MOS technology.

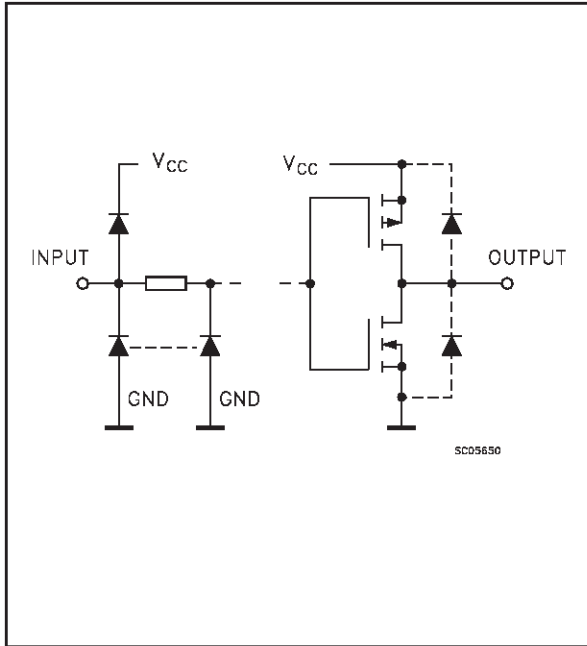
It contains two groups of 2 bit latches controlled by an enable input (G1•2 or G3•4). These two latch groups can be used in different circuits. Each latch has Q and  $\bar{Q}$  outputs (1Q - 4Q and 1 $\bar{Q}$  - 4 $\bar{Q}$ ). The data applied to the data input is transferred to the

Q and  $\bar{Q}$  outputs when the enable input is taken high and the outputs will follow the data input as long as the enable input is kept high. When the enable input is taken low, the information data applied to the data input is retained at the outputs. All inputs are equipped with protection circuits against static discharge and transient excess voltage.

### PIN CONNECTION AND IEC LOGIC SYMBOLS



INPUT AND OUTPUT EQUIVALENT CIRCUIT



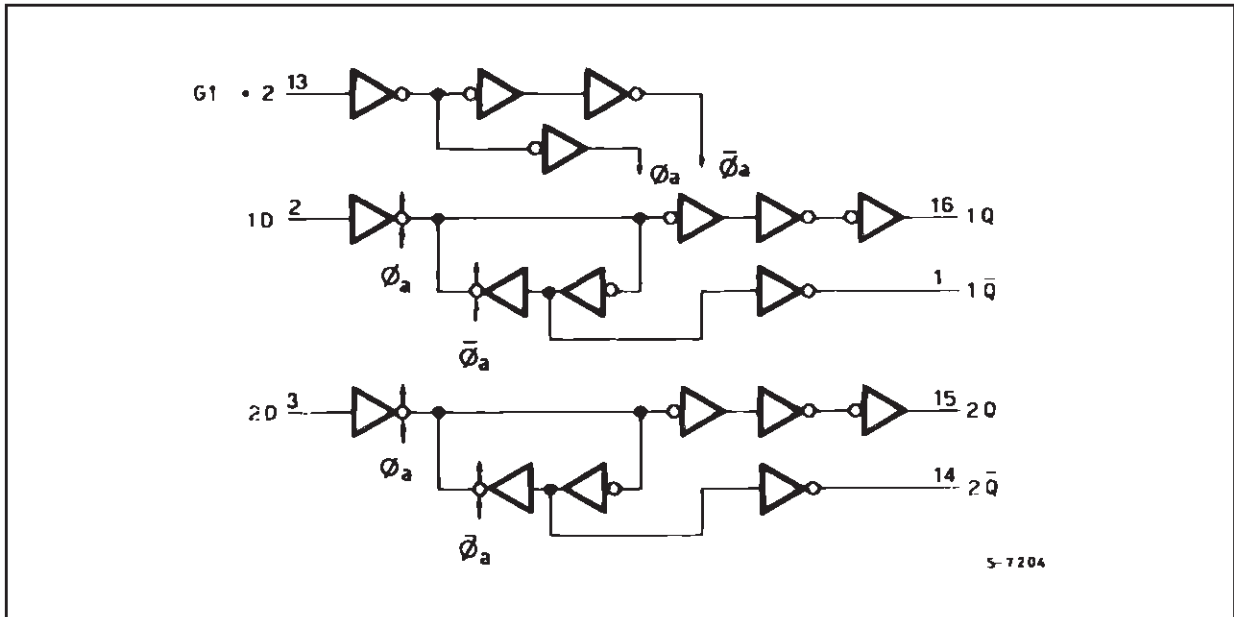
PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 14, 11, 8	1Q̄ to 4Q̄	Complementary Latch Outputs
2, 3, 6, 7	1D to 4D	Data Inputs
4	G3 • 4	Latch Enable Input, latches 3 and 4
13	G1 • 2	Latch Enable Input, latches 1 and 2
16, 15, 10, 9	1Q to 4Q	Latch Outputs
12	GND	Ground (0V)
5	V <sub>CC</sub>	Positive Supply Voltage

TRUTH TABLE

INPUTS		OUTPUTS		FUNCTION
D	G	Q	Q̄	
L	H	L	H	
H	H	H	L	
X	L	Q <sub>n</sub>	Q <sub>n</sub>	LATCH

LOGIC DIAGRAM



**ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
$V_{CC}$	Supply Voltage	-0.5 to +7	V
$V_I$	DC Input Voltage	-0.5 to $V_{CC} + 0.5$	V
$V_O$	DC Output Voltage	-0.5 to $V_{CC} + 0.5$	V
$I_{IK}$	DC Input Diode Current	$\pm 20$	mA
$I_{OK}$	DC Output Diode Current	$\pm 20$	mA
$I_O$	DC Output Current	$\pm 25$	mA
$I_{CC}$ or $I_{GND}$	DC $V_{CC}$ or Ground Current	$\pm 50$	mA
$P_D$	Power Dissipation	500(*)	mW
$T_{stg}$	Storage Temperature	-65 to +150	°C
$T_L$	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

(\*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

**RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit	
$V_{CC}$	Supply Voltage	2 to 6	V	
$V_I$	Input Voltage	0 to $V_{CC}$	V	
$V_O$	Output Voltage	0 to $V_{CC}$	V	
$T_{op}$	Operating Temperature	-55 to 125	°C	
$t_r, t_f$	Input Rise and Fall Time	$V_{CC} = 2.0V$	0 to 1000	ns
		$V_{CC} = 4.5V$	0 to 500	ns
		$V_{CC} = 6.0V$	0 to 400	ns

## DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value						Unit	
		V <sub>CC</sub> (V)		T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V <sub>IH</sub>	High Level Input Voltage	2.0		1.5			1.5		1.5		V
		4.5		3.15			3.15		3.15		
		6.0		4.2			4.2		4.2		
V <sub>IL</sub>	Low Level Input Voltage	2.0				0.5		0.5		0.5	V
		4.5				1.35		1.35		1.35	
		6.0				1.8		1.8		1.8	
V <sub>OH</sub>	High Level Output Voltage	2.0	I <sub>O</sub> =-20 μA	1.9	2.0		1.9		1.9		V
		4.5	I <sub>O</sub> =-20 μA	4.4	4.5		4.4		4.4		
		6.0	I <sub>O</sub> =-20 μA	5.9	6.0		5.9		5.9		
		4.5	I <sub>O</sub> =-4.0 mA	4.18	4.31		4.13		4.10		
		6.0	I <sub>O</sub> =-5.2 mA	5.68	5.8		5.63		5.60		
V <sub>OL</sub>	Low Level Output Voltage	2.0	I <sub>O</sub> =20 μA		0.0	0.1		0.1		0.1	V
		4.5	I <sub>O</sub> =20 μA		0.0	0.1		0.1		0.1	
		6.0	I <sub>O</sub> =20 μA		0.0	0.1		0.1		0.1	
		4.5	I <sub>O</sub> =4.0 mA		0.17	0.26		0.33		0.40	
		6.0	I <sub>O</sub> =5.2 mA		0.18	0.26		0.33		0.40	
I <sub>I</sub>	Input Leakage Current	6.0	V <sub>I</sub> = V <sub>CC</sub> or GND			± 0.1		± 1		± 1	μA
I <sub>CC</sub>	Quiescent Supply Current	6.0	V <sub>I</sub> = V <sub>CC</sub> or GND			2		20		40	μA

AC ELECTRICAL CHARACTERISTICS ( $C_L = 50 \text{ pF}$ , Input  $t_r = t_f = 6 \text{ ns}$ )

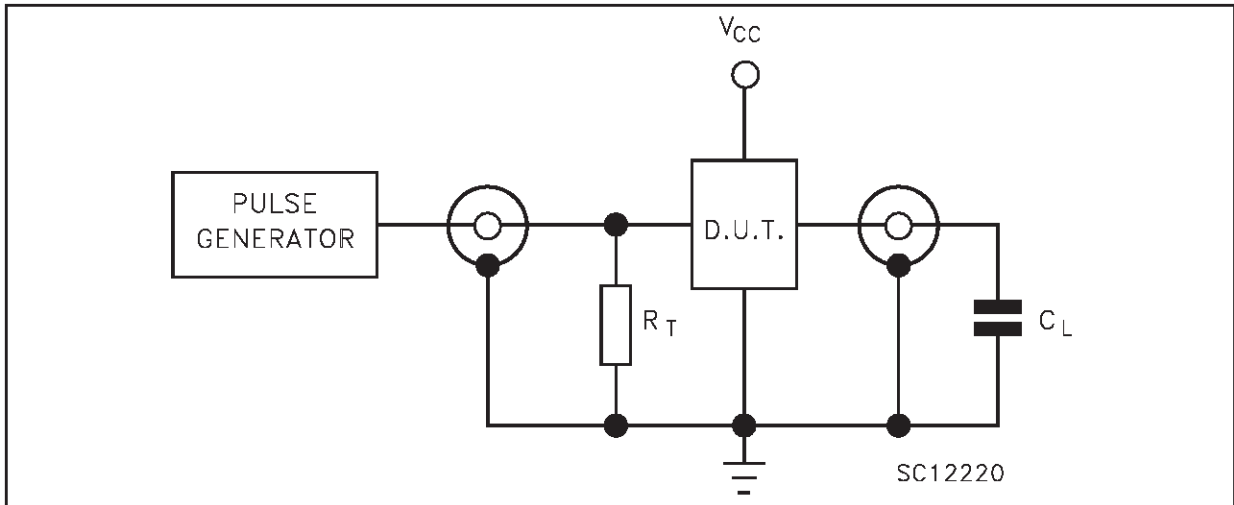
Symbol	Parameter	Test Condition		Value						Unit	
		$V_{CC}$ (V)		$T_A = 25^\circ\text{C}$			$-40 \text{ to } 85^\circ\text{C}$		$-55 \text{ to } 125^\circ\text{C}$		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
$t_{TLH}$ $t_{THL}$	Output Transition Time	2.0			25	75		95		110	ns
		4.5			7	15		19		22	
		6.0			6	13		16		19	
$t_{PLH}$ $t_{PHL}$	Propagation Delay Time (DATA - Q)	2.0			36	110		140		165	ns
		4.5			12	22		28		33	
		6.0			10	19		24		28	
$t_{PLH}$ $t_{PHL}$	Propagation Delay Time (G-Q)	2.0			40	125		155		190	ns
		4.5			13	25		31		38	
		6.0			11	21		26		32	
$t_{W(H)}$	Minimum Pulse Width (G)	2.0			18	75		95		110	ns
		4.5			6	15		19		22	
		6.0			6	13		16		19	
$t_s$	Minimum Set-up Time	2.0				50		65		75	ns
		4.5				10		13		15	
		6.0				9		11		13	
$t_h$	Minimum Hold Time	2.0				25		30		40	ns
		4.5				5		6		8	
		6.0				4		5		7	

## CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Condition		Value						Unit	
		$V_{CC}$ (V)		$T_A = 25^\circ\text{C}$			$-40 \text{ to } 85^\circ\text{C}$		$-55 \text{ to } 125^\circ\text{C}$		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
$C_{IN}$	Input Capacitance	5.0			5	10		10		10	pF
$C_{PD}$	Power Dissipation Capacitance (note 1)	5.0			30						pF

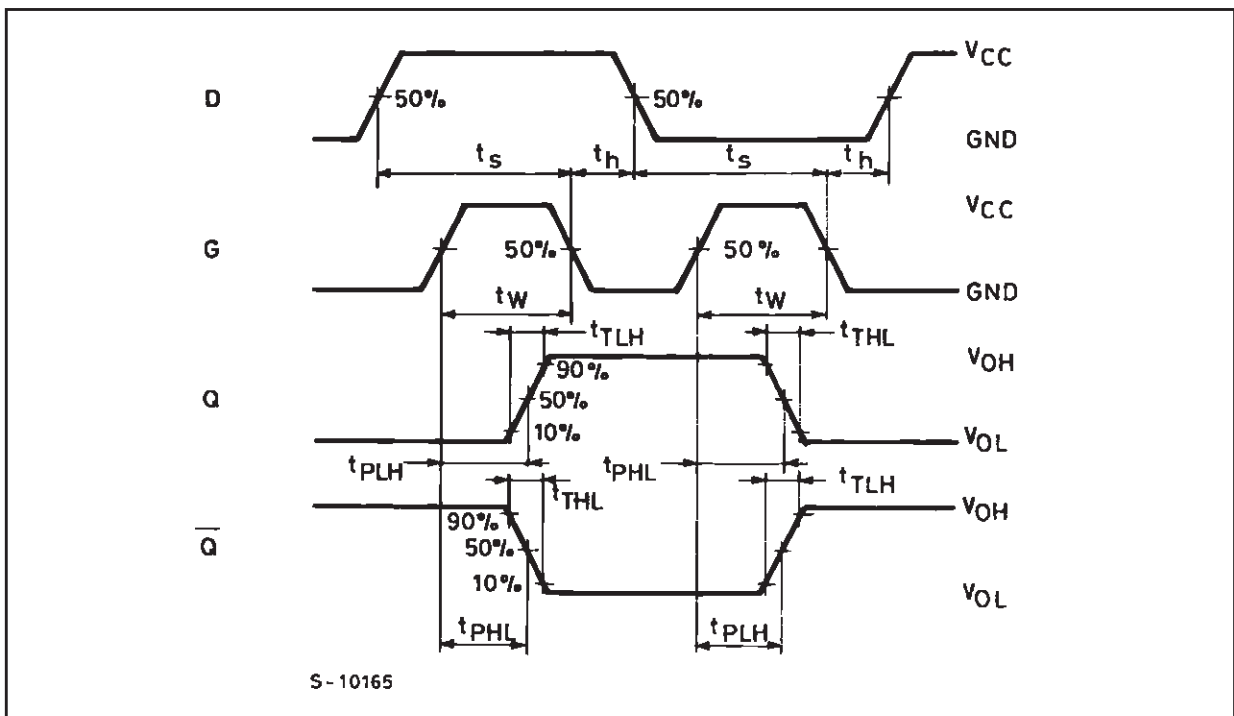
1)  $C_{PD}$  is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation.  $I_{CC(oper)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}$

TEST CIRCUIT



$C_L = 50\text{pF}$  or equivalent (includes jig and probe capacitance)  
 $R_T = Z_{OUT}$  of pulse generator (typically  $50\Omega$ )

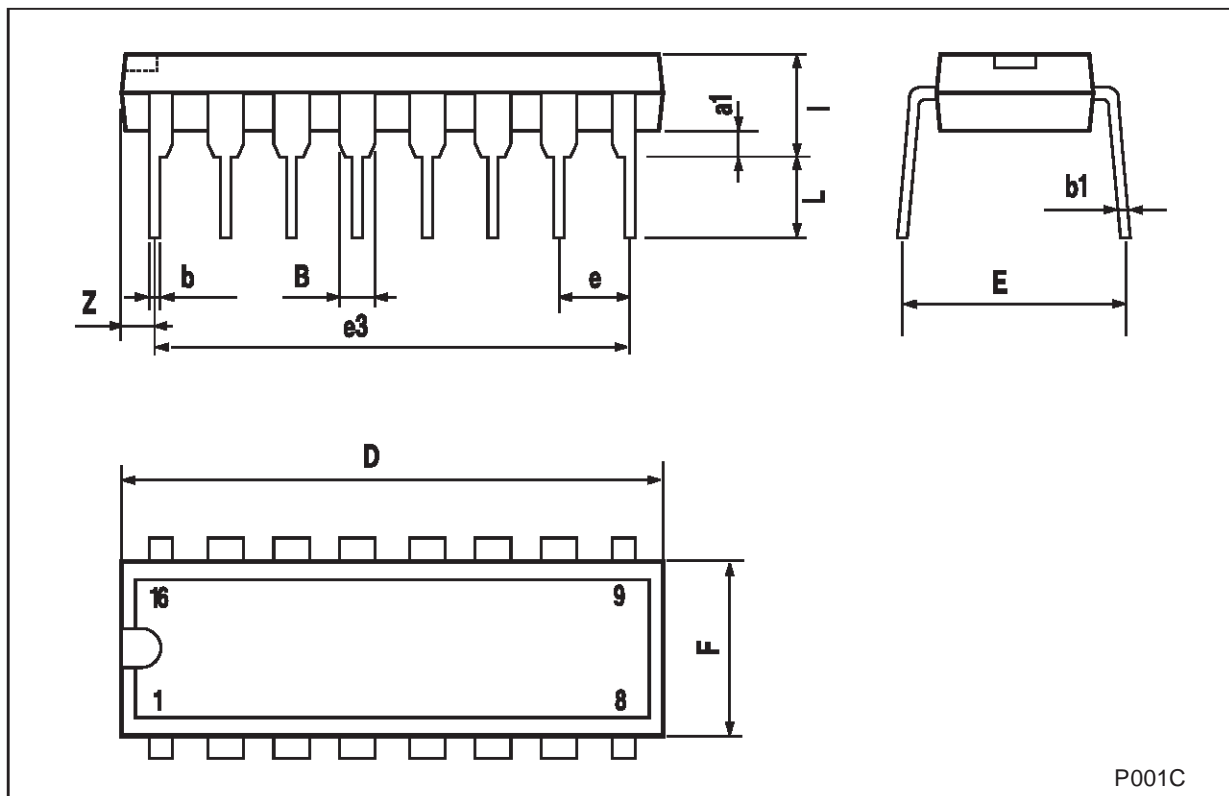
SWITCHING CHARACTERISTICS TEST WAVEFORM (f=1MHz; 50% duty cycle)



S-10165

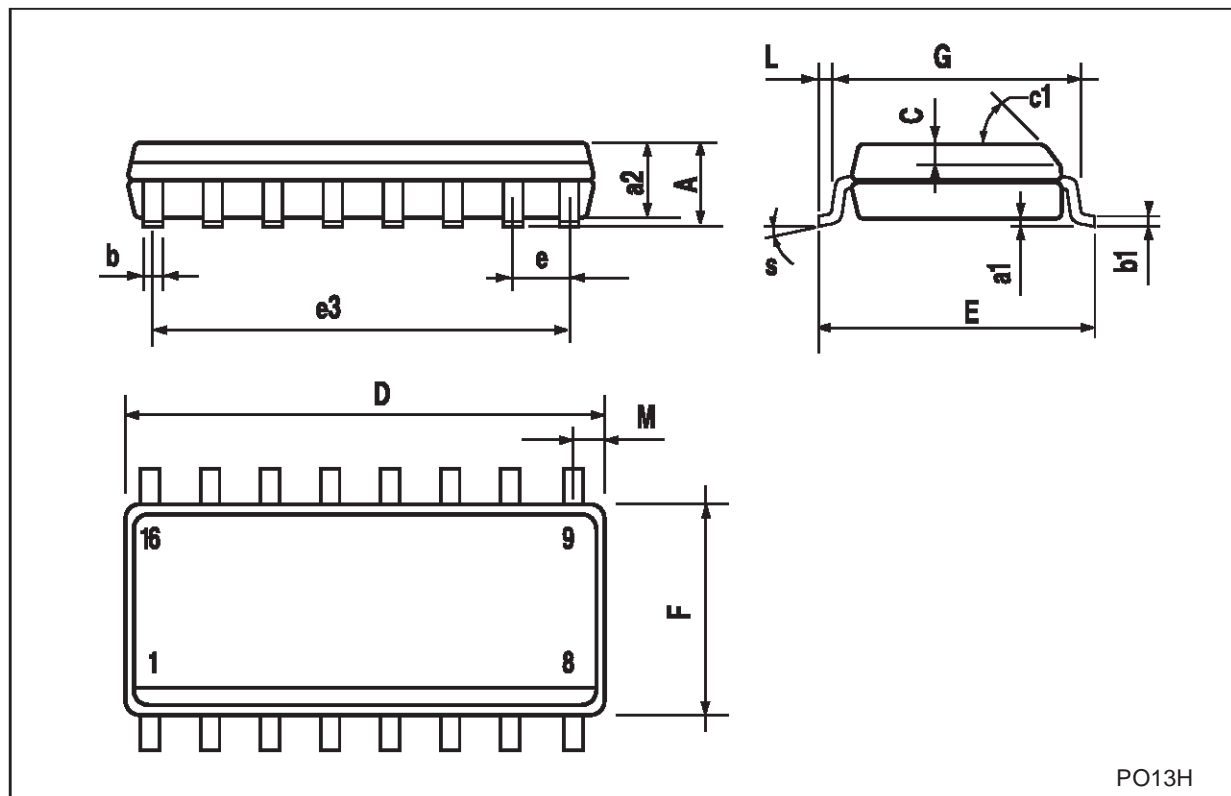
**Plastic DIP-16 (0.25) MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050



## SO-16 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	9.8		10	0.385		0.393
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.62			0.024
S	8° (max.)					

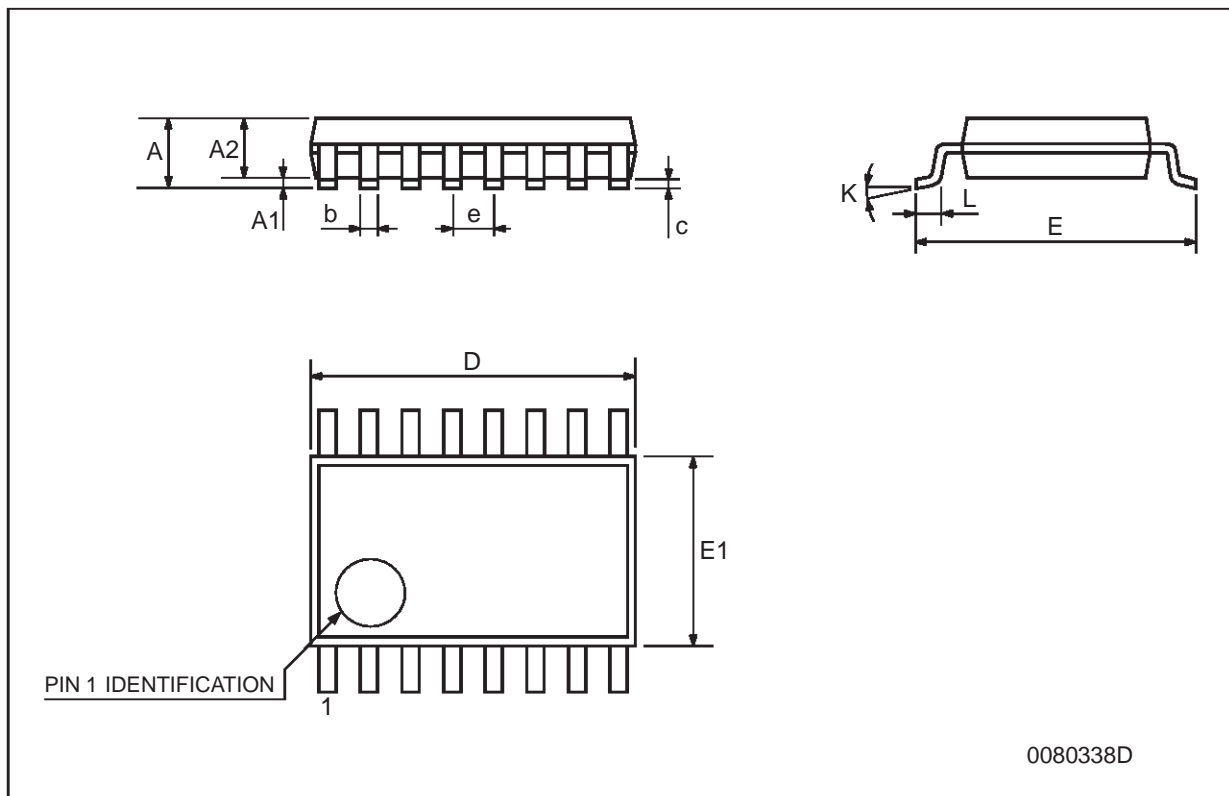


PO13H



## TSSOP16 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0089
D	4.9	5	5.1	0.193	0.197	0.201
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



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